

PNP Silicon Epibase Transistors

T-33-17

BD 612

BD 614

SIEMENS AKTIENGESELLSCHAFT 04383 D

BD 616

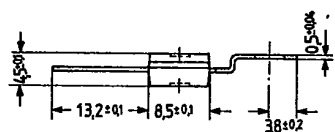
BD 618

BD 620

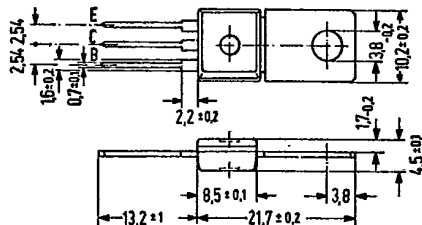
The transistors BD 612, BD 614, BD 616, BD 618, and BD 620 are PNP silicon epibase power transistors in a plastic package similar to TO 202. The collector is electrically connected to the metallic mounting area. The transistors are particularly suitable for use in push-pull output stages, driver stages as well as for general AF applications. Their complementary types are the NPN transistors BD 611, BD 613, BD 615, BD 617, and BD 619.

Type	Ordering code
BD 612	Q62702-D947
BD 614	Q62702-D949
BD 616	Q62702-D951
BD 618	Q62702-D953
BD 620	Q62702-D955

Type	Ordering code
BD 612/BD 611 pair.	Q62702-D1103
BD 614/BD 613 pair.	Q62702-D1104
BD 616/BD 615 pair.	Q62702-D1105
BD 618/BD 617 pair.	Q62702-D1106
BD 620/BD 619 pair.	Q62702-D1107



Available upon request also with bent fixing plate.



Approx. weight 15 g

Dimensions in mm

Maximum ratings

		BD 612	BD 614	BD 616	BD 618	BD 620	
Collector-emitter voltage	$-V_{CEO}$	22	32	45	60	80	V
Collector-emitter voltage	$-V_{CES}$	22	32	45	60	80	V
Collector-base voltage	$-V_{CBO}$	22	32	45	60	80	V
Emitter-base voltage	$-V_{EBO}$	5	5	5	5	5	V
Collector current	$-I_C$	4	4	4	4	4	A
Collector peak current ($t < 11$ ms)	$-I_{CM}$	7	7	7	7	7	A
Emitter peak current ($t \leq 10$ ms)	$-I_{EM}$	7	7	7	7	7	A
Base current	$-I_B$	1	1	1	1	1	A
Junction temperature	T_j	150	150	150	150	150	°C
Storage temperature range	T_{stg}	-55 to +150					°C
Total power dissipation ($T_{case} \leq 25$ °C; $V_{CE} \leq 12$ V)	P_{tot}	15	15	15	15	15	W

Thermal resistance

Junction to ambient air	R_{thJA}	$\leq 62,5$	$\leq 62,5$	$\leq 62,5$	$\leq 62,5$	$\leq 62,5$	K/W
Junction to mounting area	R_{thJC}	$\leq 8,3$	$\leq 8,3$	$\leq 8,3$	$\leq 8,3$	$\leq 8,3$	K/W

BD 612
BD 614
BD 616
BD 618
BD 620

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Static characteristics ($T_{case} = 25^{\circ}\text{C}$)

	BD 612	BD 614	BD 616	BD 618	BD 620	
Collector-emitter breakdown voltage ($-I_C = 100\text{ mA}$)	$-V_{(BR)CEO} > 22$	> 32	> 45	> 60	> 80	V
Collector-emitter breakdown voltage ($-I_C = 100\text{ }\mu\text{A}$)	$-V_{(BR)CES} > 22$	> 32	> 45	> 60	> 80	V
Collector-base breakdown voltage ($-I_C = 100\text{ }\mu\text{A}$)	$-V_{(BR)CBC} > 22$	> 32	> 45	> 60	> 80	V
Emitter-base breakdown voltage ($I_E = 1\text{ mA}$)	$-V_{(BR)EBO} > 5$	> 5	> 5	> 5	> 5	V
Collector cutoff current ($-V_{CB} = 22\text{ V}$)	$-I_{CBO} < 100$	-	-	-	-	μA
Collector cutoff current ($-V_{CB} = 32\text{ V}$)	$-I_{CBO}$	< 100	-	-	-	μA
Collector cutoff current ($-V_{CB} = 45\text{ V}$)	$-I_{CBO}$	-	< 100	-	-	μA
Collector cutoff current ($-V_{CB} = 60\text{ V}$)	$-I_{CBO}$	-	-	< 100	-	μA
Collector cutoff current ($-V_{CB} = 80\text{ V}$)	$-I_{CBO}$	-	-	-	< 100	μA
Collector cutoff current ($-V_{CB} = 10\text{ V}$; $T_{amb} = 150^{\circ}\text{C}$)	$-I_{CBO} < 1$	< 1	< 1	< 1	< 1	mA
Collector cutoff current ($-V_{CB} = V_{CBmax}$; $T_{amb} = 150^{\circ}\text{C}$)	$-I_{CBO} < 3$	< 3	< 3	< 3	< 3	mA
Base-emitter forward voltage ($-I_C = 2\text{ A}$; $-V_{CE} = 1\text{ V}$)	$-V_{BE} < 1.1$	< 1.1	< 1.2	< 1.5	< 1.5	V
Base-emitter forward voltage ($-I_C = 3\text{ A}$; $-V_{CE} = 1\text{ V}$)	$-V_{BE}$	-	< 1.3	< 1.6	< 1.6	V
Collector-emitter saturation voltage ($-I_C = 2\text{ A}$) ¹⁾	$-V_{CEsat} < 0.8$	< 0.8	-	-	-	V
Collector-emitter saturation voltage ($-I_C = 2\text{ A}$; $-I_B = 0.2\text{ A}$)	$-V_{CEsat} < 0.5$	< 0.5	< 0.6	< 0.8	< 0.8	V
Collector-emitter saturation voltage ($-I_C = 3\text{ A}$; $-I_B = 0.3\text{ A}$)	$-V_{CEsat}$	-	< 0.7	< 0.9	< 0.9	V
DC current gain ($-I_C = 10\text{ mA}$; $-V_{CE} = 5\text{ V}$)	$h_{FE} > 40$	> 40	> 30	> 20	> 15	-
($-I_C = 500\text{ mA}$; $-V_{CE} = 1\text{ V}$) ²⁾	$h_{FE} > 85$	> 85	> 85	> 40	> 40	-
($-I_C = 2\text{ A}$; $-V_{CE} = 1\text{ V}$)	$h_{FE} > 50$	> 50	> 40	> 25	> 15	-

1) For the characteristic which passes through the point $I_C = 2.2\text{ A}$ and $V_{CE} = 1\text{ V}$ at constant base current.2) Available as matching pairs with BD 611, BD 613, BD 615, BD 617, and BD 619. Condition for matching pairs $h_{FE1}/h_{FE2} \leq 1.41$.

25C D ■ 8235605 0004385 3 ■ SIEG
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BD 612
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BD 618
BD 620

Dynamic characteristics ($T_{\text{case}} = 25^{\circ}\text{C}$)

		BD 612	BD 614	BD 616	BD 618	BD 620	
Transition frequency ($-I_C = 0.25\text{ A}$; $-V_{CE} = 1\text{ V}$; $f = 1\text{ MHz}$)	f_T	>3	>3	>3	>3	>3	MHz
Cutoff frequency in common emitter configuration ($-I_C = 0.25\text{ A}$; $-V_{CE} = 1\text{ V}$)	f_{hfe}	>20	>20	>20	>20	>20	kHz

